

MHW592

The RF Line

LOW DISTORTION WIDEBAND AMPLIFIER

... low-noise, high-gain, ultra-linear, thin-film hybrid. Designed for multi-purpose broadband 50 to 100 ohm system applications requiring superior gain and current stability with temperature.

- Supply Voltage = 24 V Nominal
- Broadband Power Gain –
 $G_p = 35 \text{ dB (Typ) @ } f = 1\text{-}250 \text{ MHz}$
- Broadband Noise Figure –
 $NF = 3.6 \text{ dB (Typ) @ } f = 30 \text{ MHz}$
- Ideal for Low Level Wideband Linear Amplifiers and AM Modulators in HF/SSB, VHF Communications Equipment and RF Instrumentation Applications

MAXIMUM RATINGS

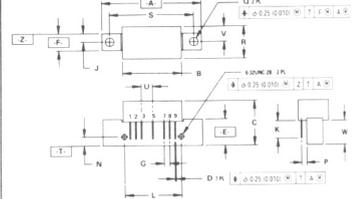
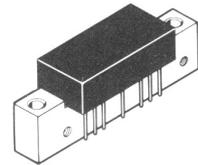
Rating	Symbol	Value	Unit
Supply Voltage	V_{DC}	28	Vdc
Input Power	P_{in}	5.0	dBm
Operating Case Temperature Range	T_C	-20 to +90	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	-40 to +100	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($V_{DC} = 24 \text{ Vdc}$, $Z_0 = 50 \Omega$, $T_C = 25^{\circ}\text{C}$. All characteristics guaranteed over bandwidth listed under "Frequency Range", unless specified otherwise.)

Characteristic	Symbol	Min	Typ	Max	Unit
Frequency Range	BW	1.0	—	250	MHz
Power Gain	G_p	33.5	35	36.5	dB
Gain Flatness	F	—	—	± 1.0	dB
Voltage Standing Wave Ratio, In/Out ($f = 1.0\text{-}30 \text{ MHz}$) ($f = 30\text{-}250 \text{ MHz}$)	VSWR	—	1.5:1 2:1	—	—
1 dB Compression ($f = 30 \text{ MHz}$) ($f = 100 \text{ MHz}$) ($f = 250 \text{ MHz}$)	P1	750	900	—	mW
Peak Envelope Power (IMD3 = -30 dB, $f = 30 \text{ MHz}$) (IMD3 = -30 dB, $f = 100 \text{ MHz}$) (IMD3 = -30 dB, $f = 250 \text{ MHz}$)	PEP	700	850	—	mW
Noise Figure ($f = 30 \text{ MHz}$) ($f = 100 \text{ MHz}$) ($f = 250 \text{ MHz}$)	NF	—	3.6 3.7 3.9	5.0	dB
DC Voltage	V_{DC}	—	24	28	V
DC Current	I_{DC}	—	300	340	mA

1.0–250 MHz

HIGH GAIN AMPLIFIER



STYLE 1
 PIN 1 RF INPUT
 2 GROUND
 3 GROUND
 4 DELETED
 5 VDC
 6 DELETED
 7 GROUND
 8 GROUND
 9 RF OUTPUT

NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982
 2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	—	45.08	—	1.775
B	26.42	26.92	1.040	1.060
C	20.57	21.34	0.810	0.840
D	0.46	0.56	0.018	0.022
E	11.81	12.95	0.465	0.510
F	7.62	8.25	0.300	0.325
G	2.54 BSC	—	0.100 BSC	—
J	3.96 BSC	—	0.156 BSC	—
K	8.00	8.50	0.315	0.335
L	25.40 BSC	—	1.00 BSC	—
N	4.19 BSC	—	0.165 BSC	—
P	2.54 BSC	—	0.100 BSC	—
Q	3.76	4.27	0.148	0.168
R	—	15.11	—	0.595
S	38.10 BSC	—	1.500 BSC	—
U	5.08 BSC	—	0.200 BSC	—
V	7.11 BSC	—	0.280 BSC	—
W	11.05	11.43	0.435	0.450

CASE 714-04

FIGURE 1 – POWER GAIN versus FREQUENCY

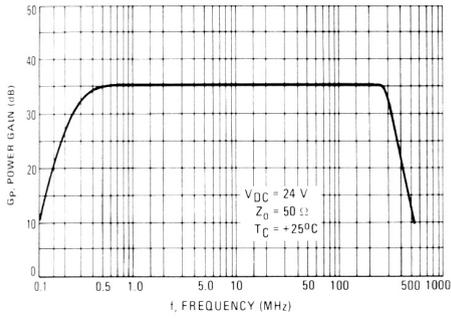


FIGURE 2 – POWER GAIN versus FREQUENCY

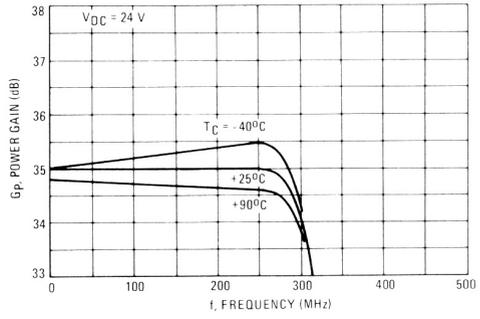


FIGURE 3 – POWER GAIN versus SUPPLY VOLTAGE

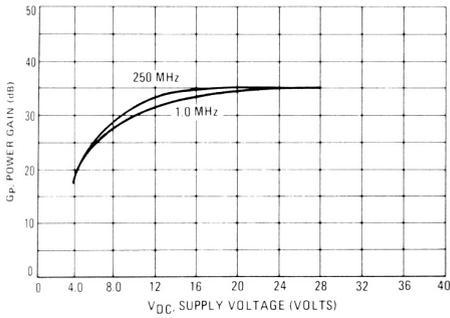


FIGURE 4 – NOISE FIGURE versus SUPPLY VOLTAGE

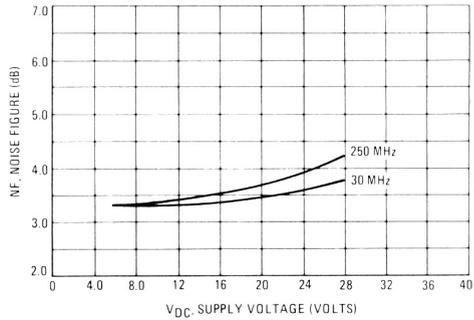


FIGURE 5 – OUTPUT POWER versus INPUT POWER

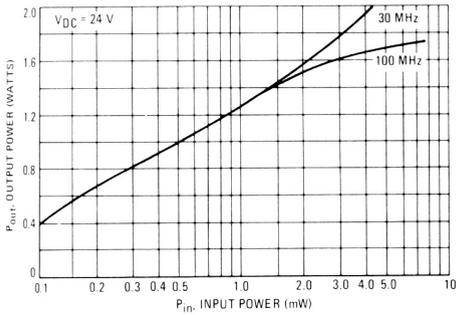


FIGURE 6 – OUTPUT POWER versus INPUT POWER

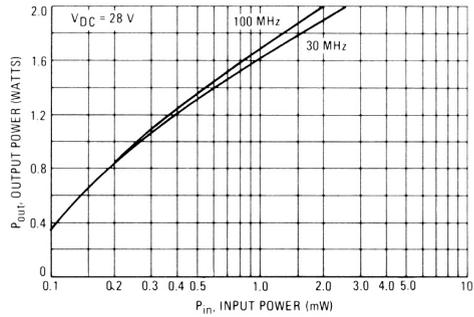


FIGURE 7 – INTERMODULATION DISTORTION versus OUTPUT POWER

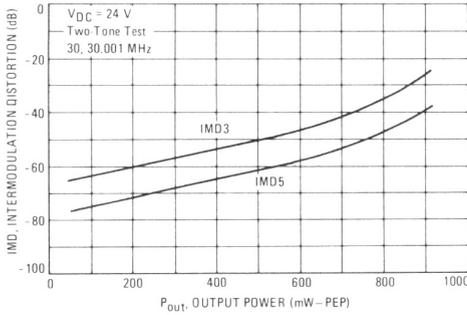


FIGURE 8 – INTERMODULATION DISTORTION versus OUTPUT POWER

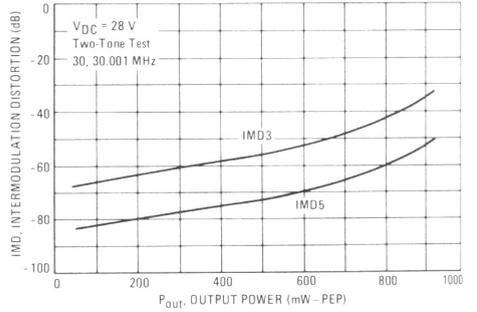
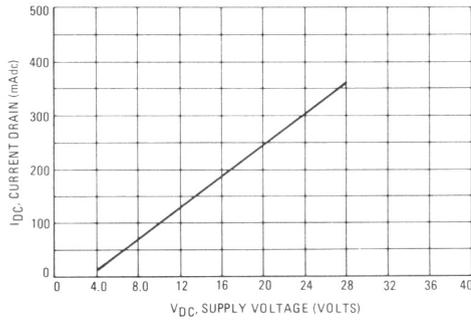


FIGURE 9 – DC CURRENT DRAIN versus SUPPLY VOLTAGE



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